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SEMICONDUCTOR



ESD



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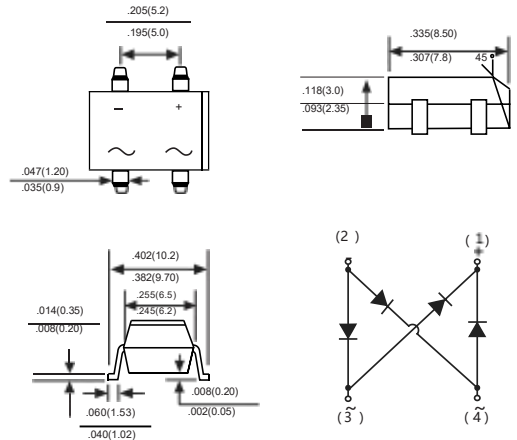
PLED

Product data sheet
Product data sheet

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Features

- Ideal for printed circuit board
- Reliable low cost construction utilizing molded plastic technique
- High temperature soldering guaranteed: 260°/10 seconds at 5 lbs., (2.3kg) tension
- Small size, simple installation
- High surge current capability



Dimensions in inches and (millimeters)

Mechanical Data

- Case** : JEDEC DBS Molded plastic body
- Terminals** : Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity** : Polarity symbol marking on case
- Mounting Position** : Any
- Weight** : 0.02 ounce, 0.4 grams

REEL SPECIFICATION

P/N	PKG	QTY
DB101S-DB107S	DBS	1500

Maximum Ratings And Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter	SYMBOLS	DB101S	DB102S	DB103S	DB104S	DB105S	DB106S	DB107S	UNITS
Marking Code									
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward rectified current at $T_C=40^\circ C$	$I_{F(AV)}$	1.0							A
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	50							A
Maximum instantaneous forward voltage drop per leg at 1A	V_F	1.1							V
Maximum DC reverse current at rated DC blocking voltage $T_A=25^\circ C$ $T_A=100^\circ C$	I_R	10 500							μA μA
Operating temperature range	T_J	-55 to +150							$^\circ C$
storage temperature range	T_{STG}	-55 to +150							$^\circ C$

NOTES: DBS for surface mount package.

atings And Characteristic Curves

FIG. 1- MAXIMUM DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

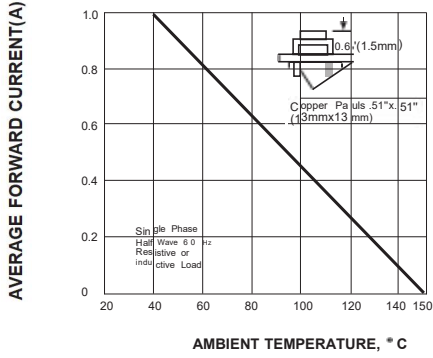


FIG. 2- MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

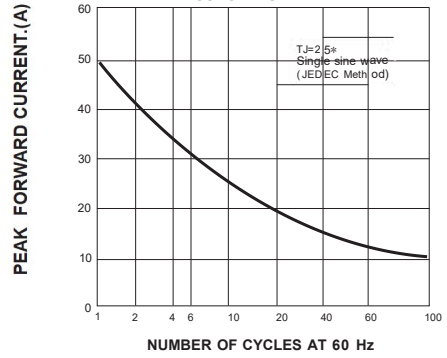


FIG. 3- TYPICAL REVERSE CHARACTERISTICS PER BRIDGE ELEMENT

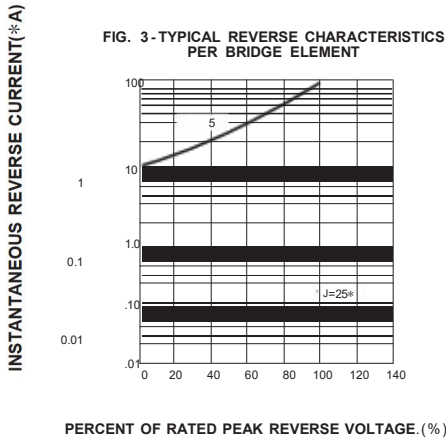


FIG. 4- TYPICAL FORWARD CHARACTERISTICS PER BRIDGE ELEMENT

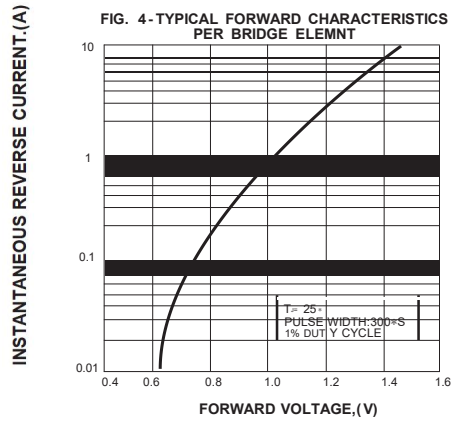
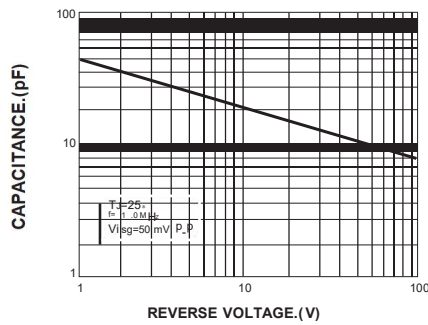


FIG. 3- TYPICAL JUNCTION CAPACITANCE PER BRIDGE ELEMENT



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